

# Schottky Diode

## **MBR735**

35V / 7,5A

# DATASHEET

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OEM – General Semiconductor

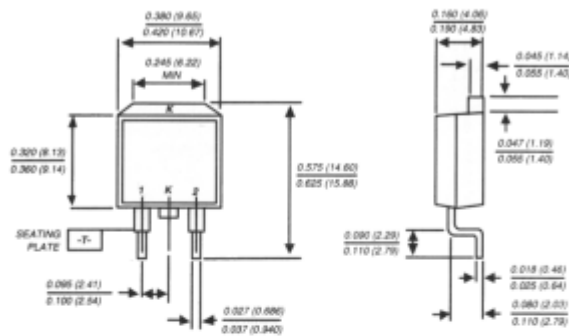
Source: General Semiconductor Databook 1998

# MBRB735 THRU MBRB760

## SCHOTTKY RECTIFIER

Reverse Voltage - 35 to 60 Volts Forward Current - 7.5 Amperes

### TO-263AB



Dimensions in inches and (millimeters)

### FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- ◆ Metal silicon junction majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ High current capability, low forward voltage drop
- ◆ High surge capability
- ◆ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ◆ Guardring for overvoltage protection
- ◆ High temperature soldering in accordance with CECC 802 / Reflow guaranteed



### MECHANICAL DATA

**Case:** JEDEC TO-263AB molded plastic body  
**Terminals:** Lead solderable per MIL-STD-750, Method 2026  
**Polarity:** As marked  
**Mounting Position:** Any  
**Weight:** 0.08 ounces, 2.24 grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	MBRB735	MBRB745	MBRB750	MBRB760	UNITS
Maximum repetitive peak reverse voltage	$V_{RRM}$	35	45	50	60	Volts
Maximum working peak reverse voltage	$V_{RWM}$	35	45	50	60	Volts
Maximum DC blocking voltage	$V_{DC}$	35	45	50	60	Volts
Maximum average forward rectified current (SEE FIG 1)	$I_{(AV)}$	7.5				Amps
Peak repetitive forward current (square wave, 20 KHz) at $T_C=105^\circ\text{C}$	$I_{FRM}$	15.0				Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	150.0				Amps
Peak repetitive reverse surge current (NOTE 1)	$I_{RRM}$	1.0		0.5		Amps
Maximum instantaneous forward voltage at (NOTE 2)	$V_F$	-		0.75		Volts
		0.57		0.65		
		0.84		-		
		0.72		-		
Maximum instantaneous reverse current at rated DC blocking voltage (NOTE 1)	$I_R$	0.1		0.5		mA
		15.0		50.0		
Voltage rate of change (rated $V_R$ )	$dv/dt$	10,000		1,000		V/ $\mu\text{s}$
Maximum thermal resistance, (NOTE 3)	$R_{\theta JC}$	3.0				$^\circ\text{C}/\text{W}$
Operating junction temperature range	$T_J$	-65 to +150				$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-65 to +175				$^\circ\text{C}$

**NOTES:**

- (1) 2.0 $\mu\text{s}$ , pulse width, f=1.0 KHz
- (2) Pulse test: 300 $\mu\text{s}$  pulse width, 1% duty cycle
- (3) Thermal resistance from junction to case

**RATINGS AND CHARACTERISTIC CURVES MBRB735 THRU MBRB760**

